A DEVICE HAVING MULTIPLE SILICIDE TYPES AND A METHOD FOR ITS FABRICATION

ABSTRACT

Provided is a semiconductor device and a method for its fabrication. The device includes a semiconductor substrate, a first silicide in a first region of the substrate, and a second silicide in a second region of the substrate. The first silicide may differ from the second silicide. The first silicide and the second silicide may be an alloy silicide.



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